Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832
Email & Skype: info@chipsmall.com Web: www.chipsmall.com
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

Ordering number:EN2791B

DCG010

Silicon Epitaxial Planar Type (Cathode Common)

Ultrahigh-Speed Switching Diode

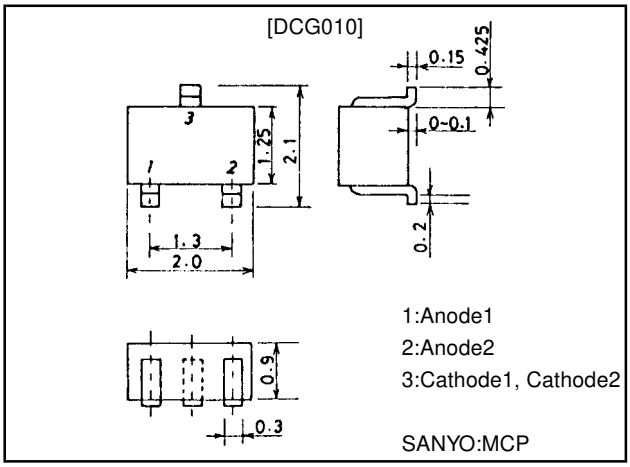
Features

- Ideally suited for use in hybrid ICs because of very small-sized package.
- Fast switching speed.
- Small interterminal capacitance.

Package Dimensions

unit:mm

1187A



Specifications

Absolute Maximum Ratings at Ta = 25°C

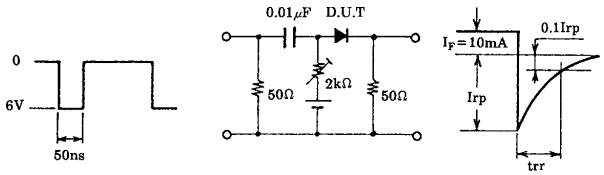
Parameter	Symbol	Conditions	Ratings	Unit
Peak Reverse Voltage	V_{RM}		85	V
Reverse Voltage	V_R		80	V
Peak Forward Current	I_{FM}	Unit rating	300	mA
		Total rating	450	mA
Average Rectified Current	I_O	Unit rating	100	mA
		Total rating	150	mA
Surge Current(1μs)	I_{FSM}	Unit rating	4	A
		total rating	6	A
Allowable Power Dissipation	P		100	mW
Junction Temperature	Tj		125	°C
Storage Temperature	Tstg		–55 to +150	°C

Electrical Characteristics at Ta = 25°C

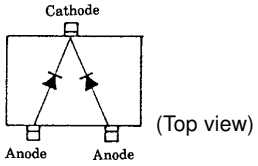
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Forward Voltage	V_{F1}	I_F=1mA		0.60		V
	V_{F2}	I_F=10mA		0.72		V
	V_{F3}	I_F=100mA			1.20	V
Reverse Current	I_{R1}	V_R=30V			0.1	μA
	I_{R2}	V_R=80V			0.5	μA
Interterminal Capacitance	C	V_R=0V, f=1MHz			3.0	pF
Reverse Recovery Time	trr	I_F=10mA, V_R=6V, R_L=50Ω, I_{rr}=0.1Irp			4.0	ns

Marking:W6

Reverse Recovery Time Test Circuit



Electrical Connection



(Top view)